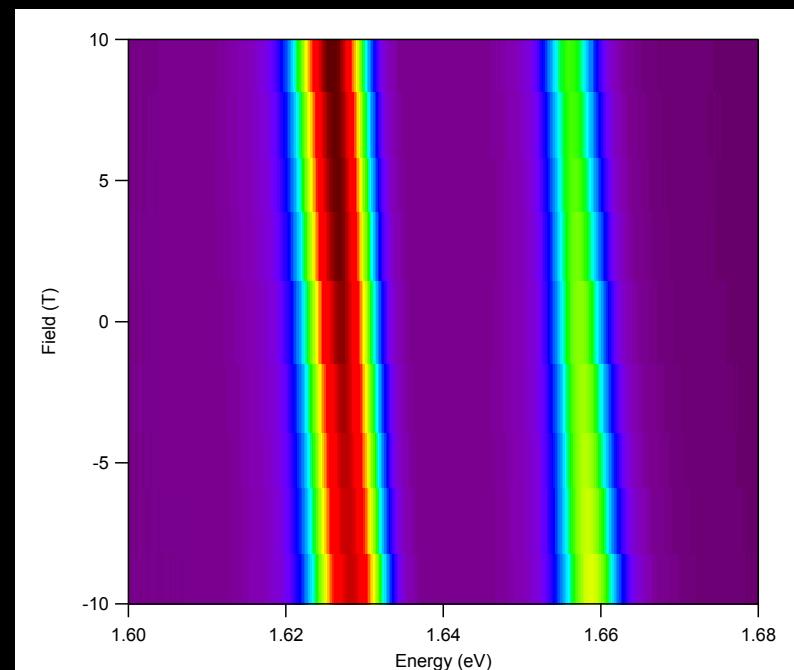
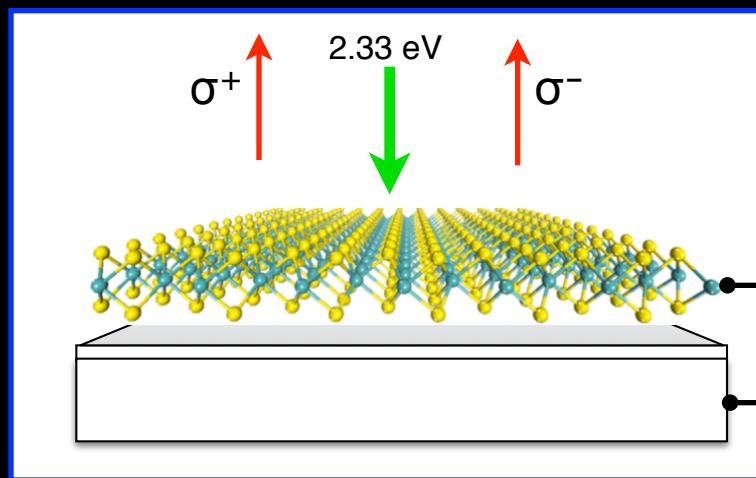
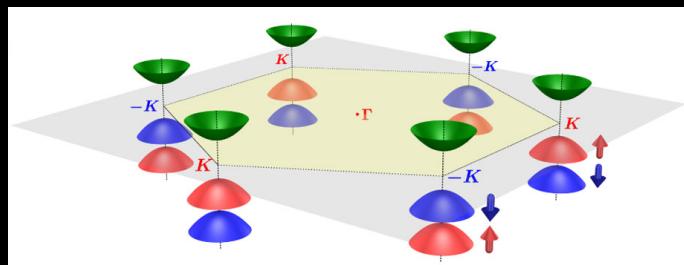


Magneto-spectroscopy of excitons in monolayer transition metal dichalcogenides

Valley splitting and polarization by magnetic field in monolayer MoSe₂



Dmitry Smirnov

National High Magnetic Field Laboratory, Tallahassee, FL

Magneto-spectroscopy of excitons in monolayer transition metal dichalcogenides

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Li, Y., Ludwig, J. et al. Phys. Rev. Lett. **113**, 266804 (2014).

Columbia University, New York NY (USA)

Yilei Li

Tony Low

Alexey Chernikov

Xu Cui

Ghidewon Arefe

Young Duck Kim

Arend van der Zande

Albert Rigosi

Heather Hill

Suk Hyun Kim

James Hone

Tony Heinz

NHMFL

Jonathan Ludwig

Zhengguang Lu

Zhiqiang Li

Dmitry Smirnov



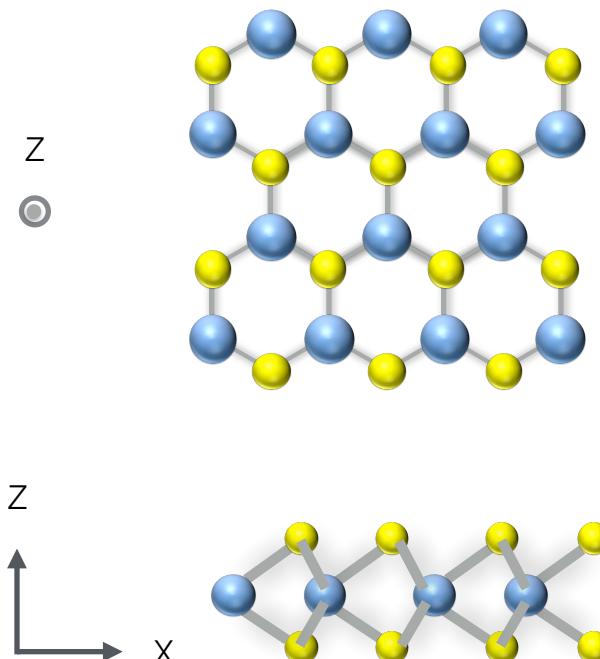
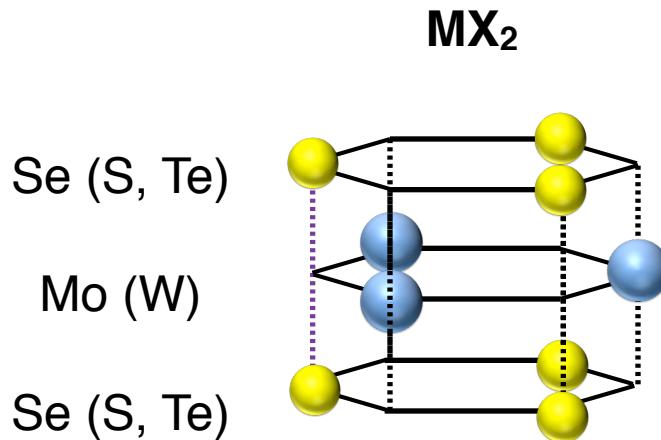
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NHMFL UCGP No. 5087



DE-SC0001085
DE-FG02-07ER46451



Semiconducting monolayer TMDs



Bulk MoS₂ : indirect-gap

From indirect gap (bulk) to direct bandgap in monolayer

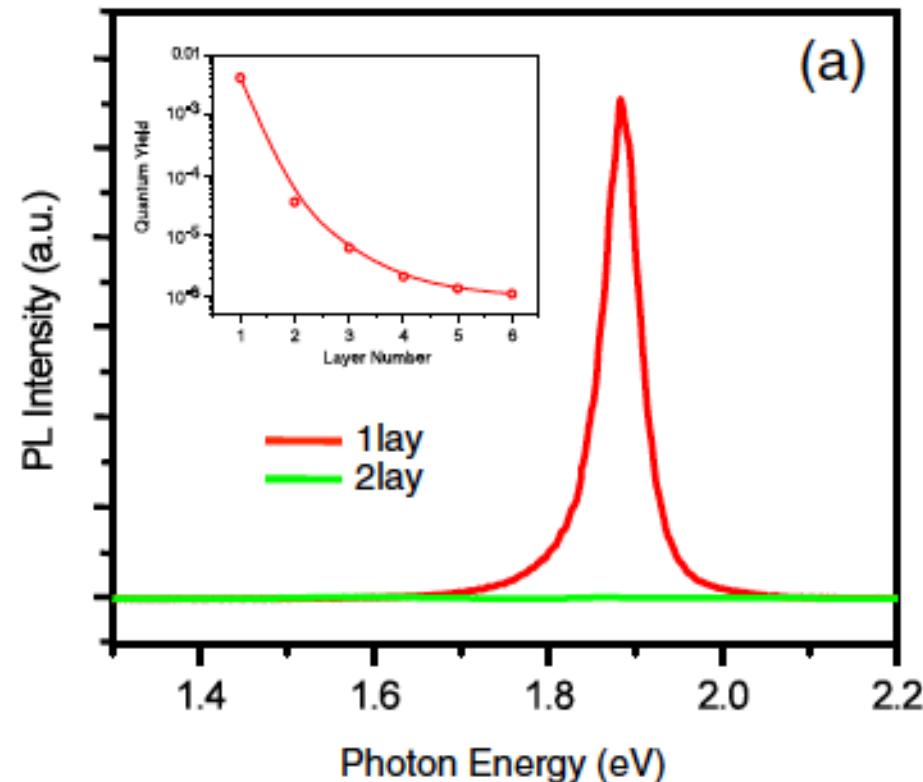
PRL 105, 136805 (2010)

PHYSICAL REVIEW LETTERS

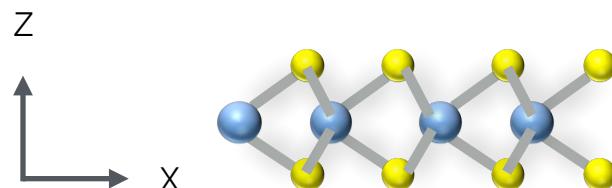
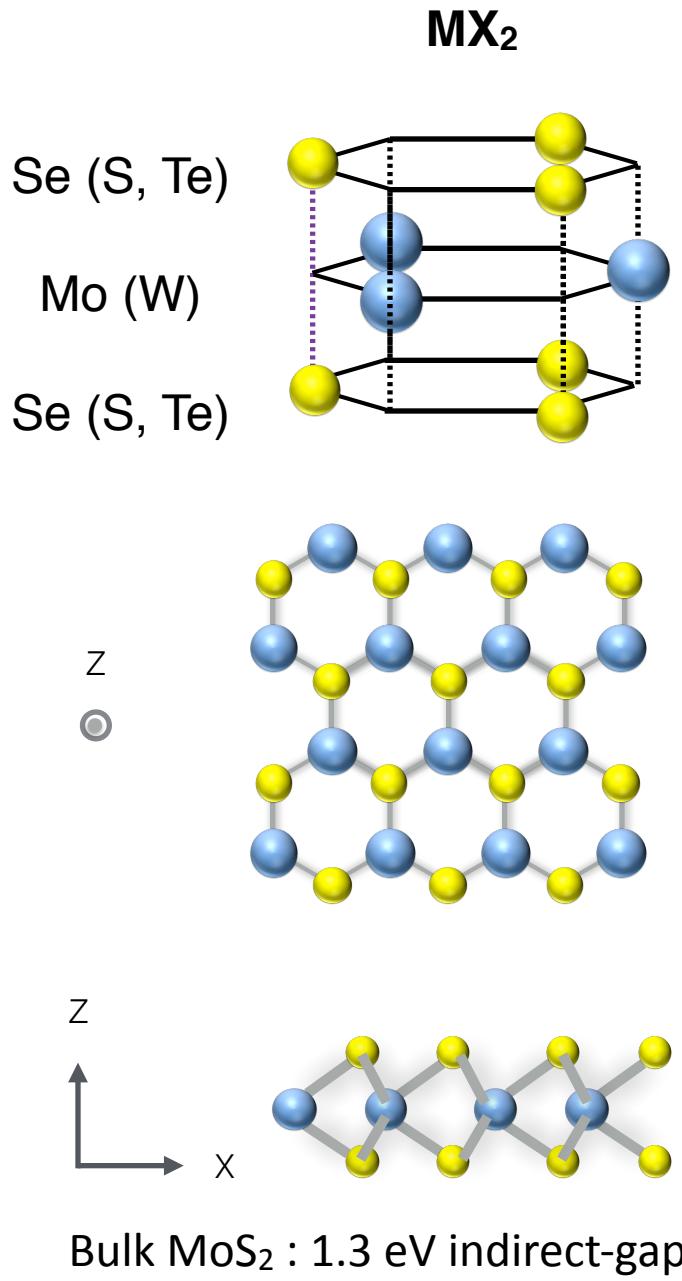
week ending
24 SEPTEMBER 2010

Atomically Thin MoS₂: A New Direct-Gap Semiconductor

Kin Fai Mak,¹ Changgu Lee,² James Hone,³ Jie Shan,⁴ and Tony F. Heinz^{1,*}

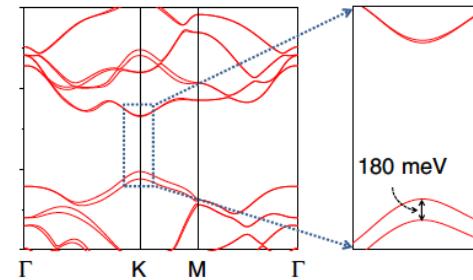


Semiconducting monolayer TMDs

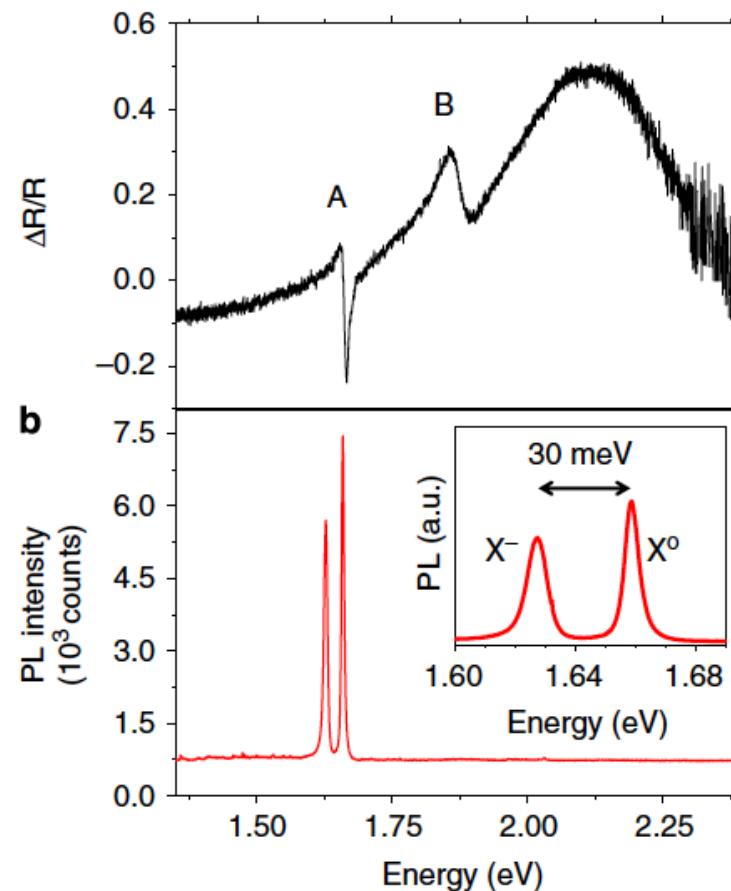


Bulk MoS₂ : 1.3 eV indirect-gap

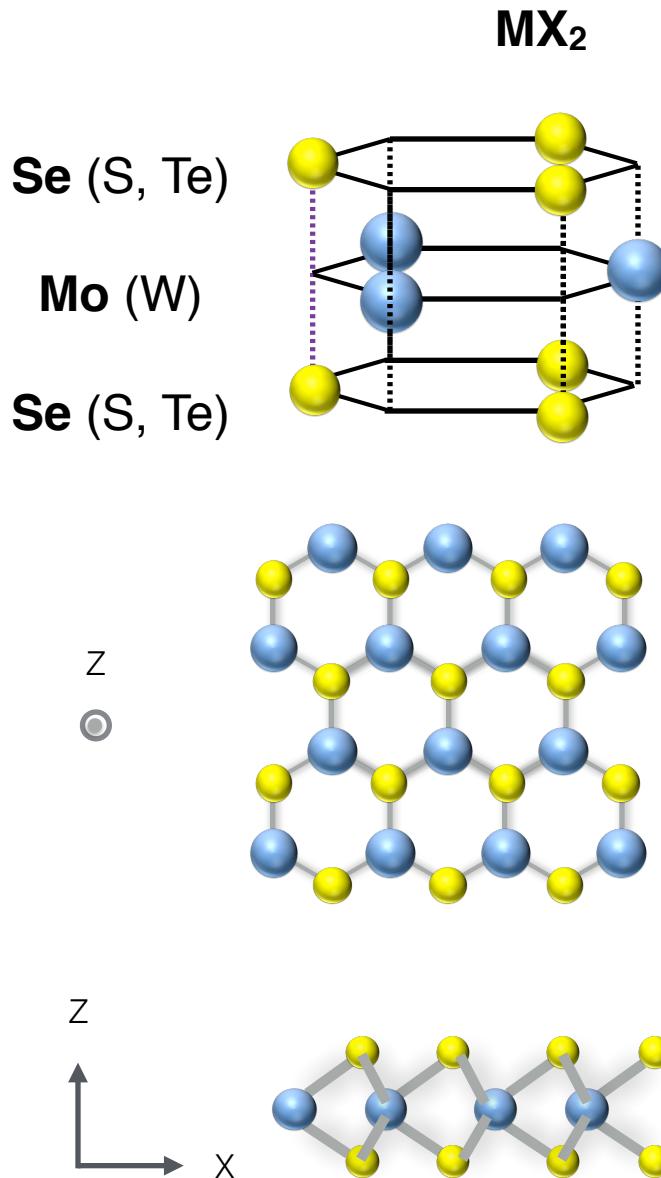
From indirect gap (bulk) to direct bandgap in monolayer



Ross et al. Nature Comm., 4:1474 (2013)



Semiconducting monolayer TMDs



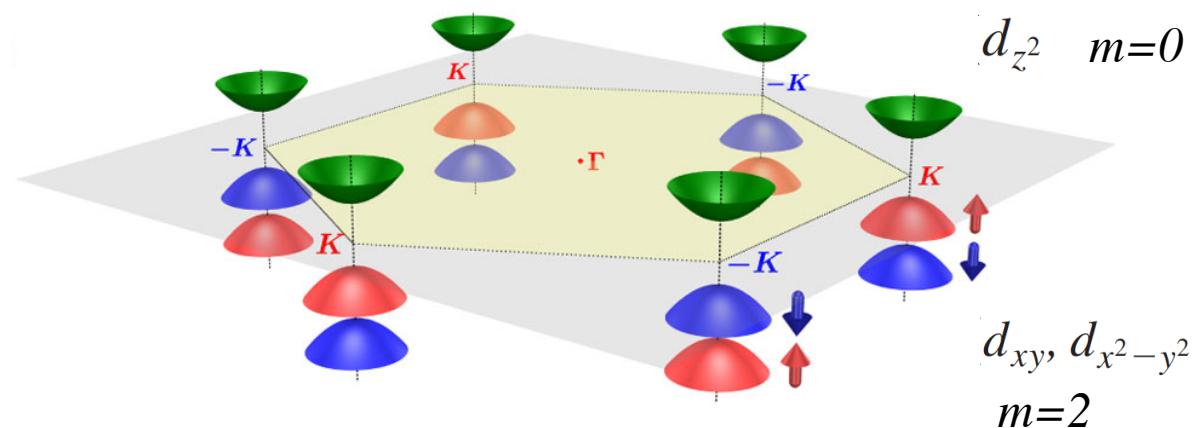
PRL 108, 196802 (2012)

PHYSICAL REVIEW LETTERS

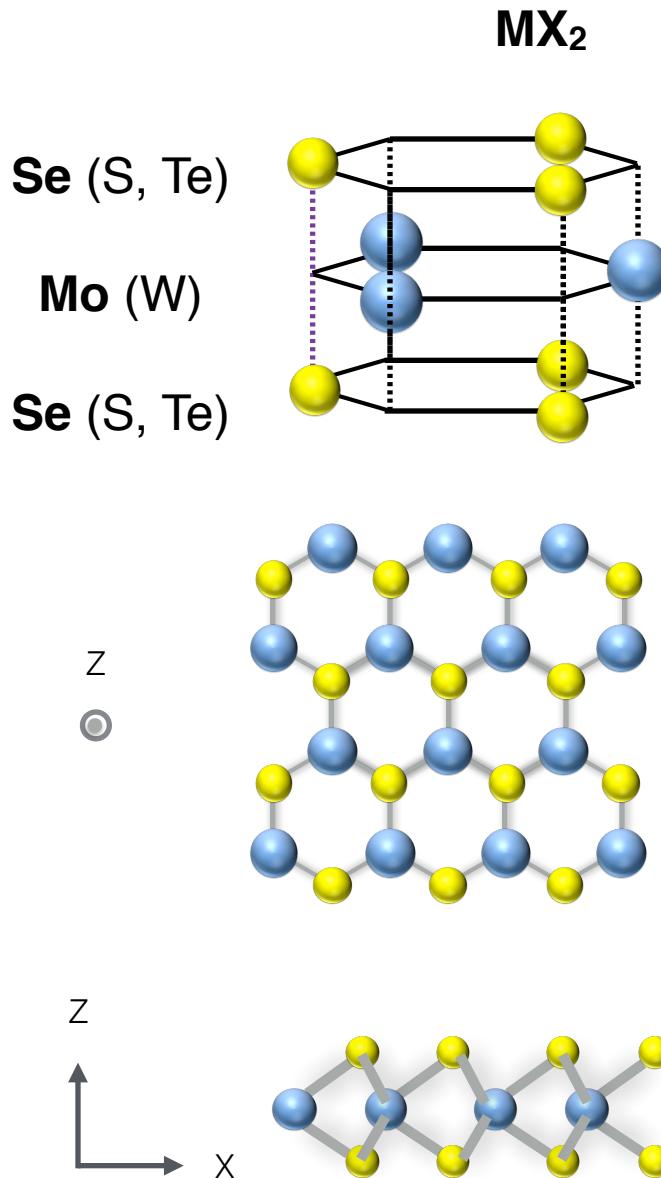
week ending
11 MAY 2012

Coupled Spin and Valley Physics in Monolayers of MoS₂ and Other Group-VI Dichalcogenides

Di Xiao,^{1,*} Gui-Bin Liu,² Wanxiang Feng,^{1,3,4} Xiaodong Xu,^{5,6} and Wang Yao^{2,†}



Semiconducting monolayer TMDs



PRL 108, 196802 (2012)

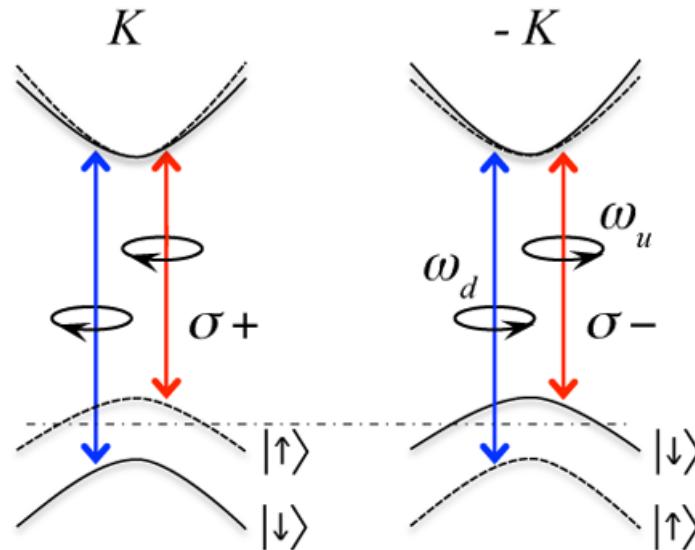
PHYSICAL REVIEW LETTERS

week ending
11 MAY 2012

Coupled Spin and Valley Physics in Monolayers of MoS₂ and Other Group-VI Dichalcogenides

Di Xiao,^{1,*} Gui-Bin Liu,² Wanxiang Feng,^{1,3,4} Xiaodong Xu,^{5,6} and Wang Yao^{2,†}

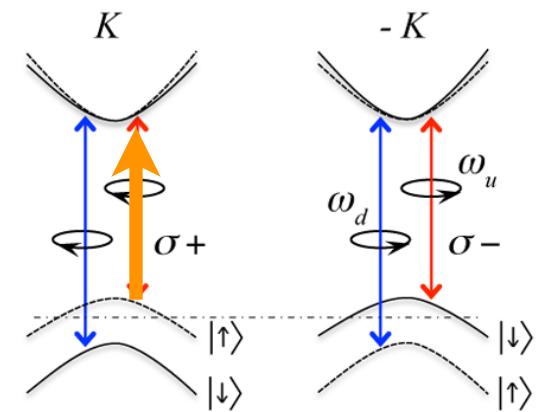
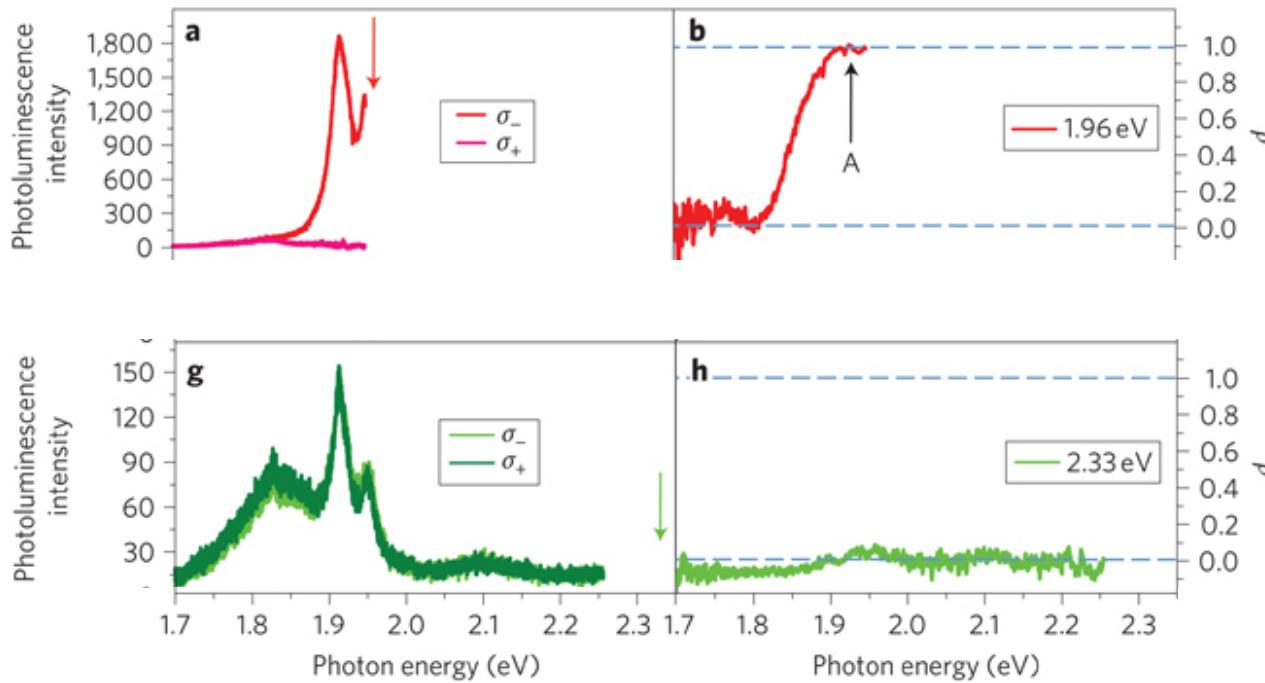
Spin-valley coupling



Valley-spin coupling

Circular Polarized PL at Resonance Excitation

- ▶ Strong polarization selectivity, preservation of circular state
- ▶ Creation of transient valley population imbalance



Mak, K. F., He, K., Shan, J., & Heinz, T. F. Nature Nanotechnol, 7, 494 (2012)
Also experiments by X. Cui, J. Feng, B. Urbaszek groups

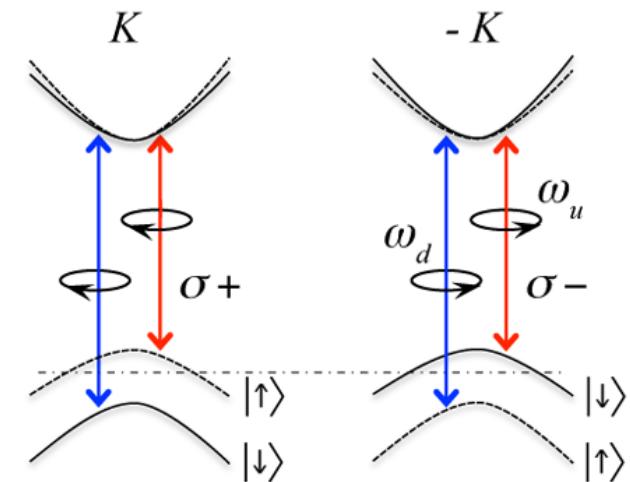
Valley-spin coupling

Circular Polarized PL at Resonance Excitation

- ▶ Strong polarization selectivity, preservation of circular state
- ▶ Creation of transient valley population imbalance

Open questions (motivation):

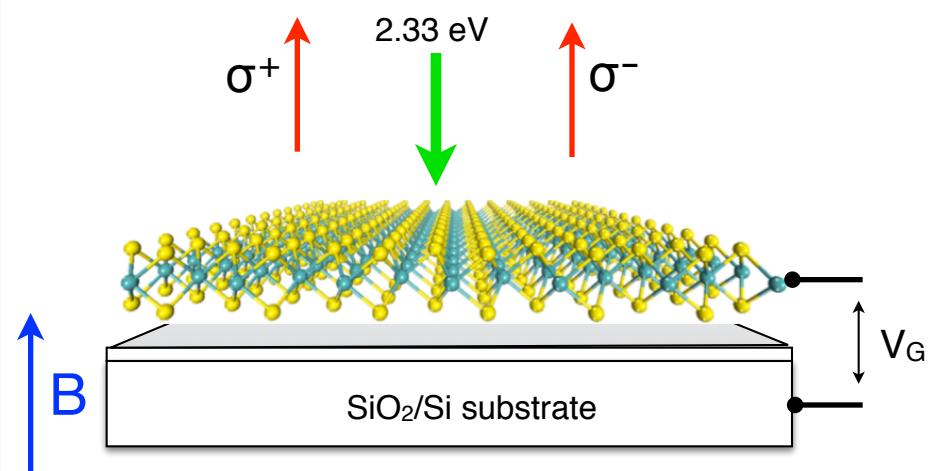
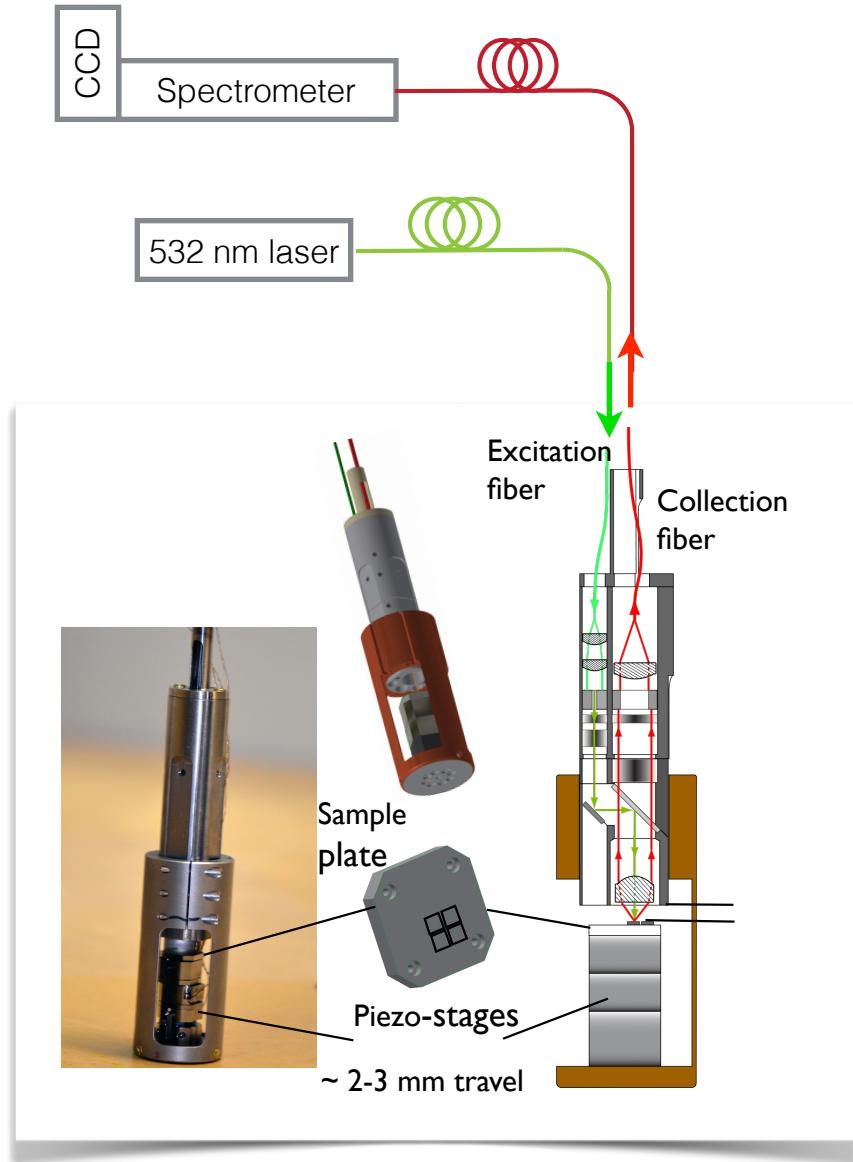
- How to break the valley degeneracy and control the valley splitting?
- How to create and control the steady-state valley polarization



Answer (method):

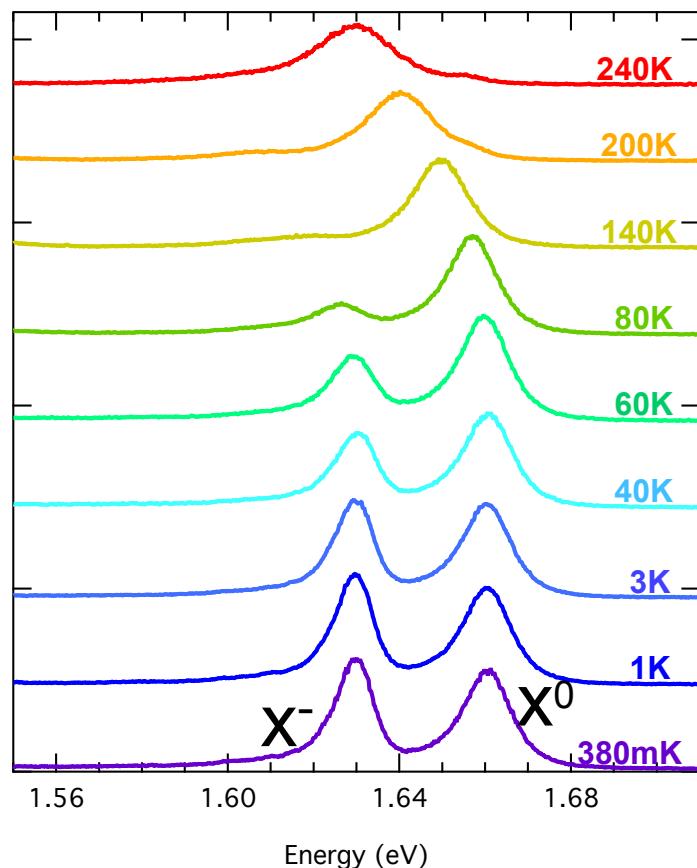
- Apply magnetic field and break the time reversal symmetry

Experimental details

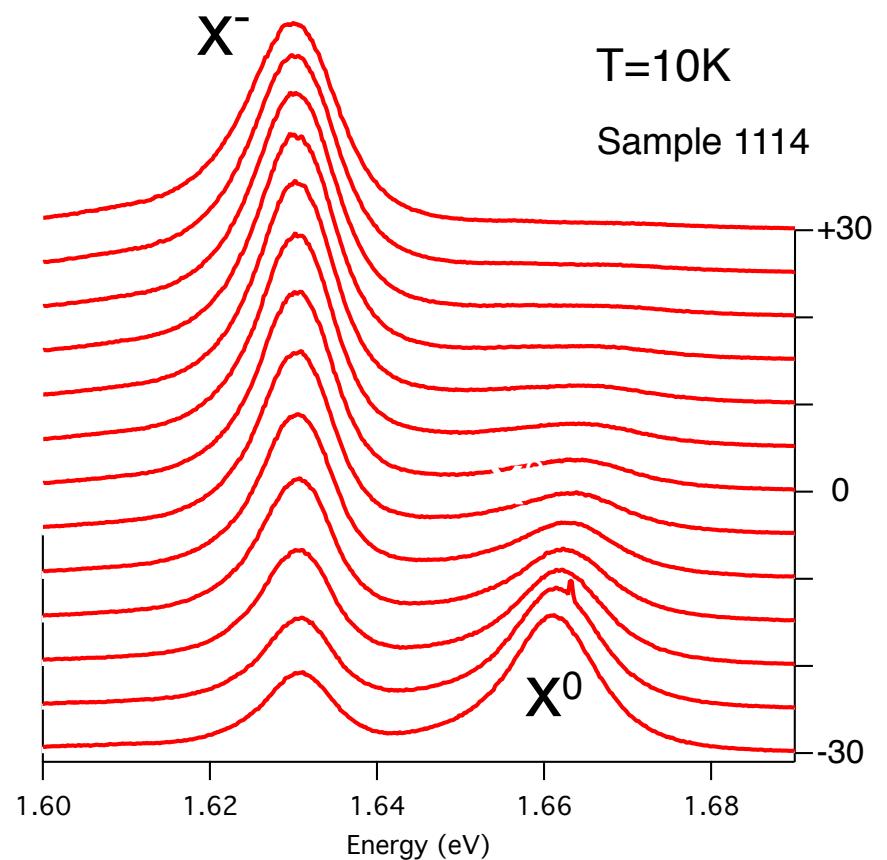


Gate control of neutral and charged excitons in a monolayer MoSe₂

Temperature dependence



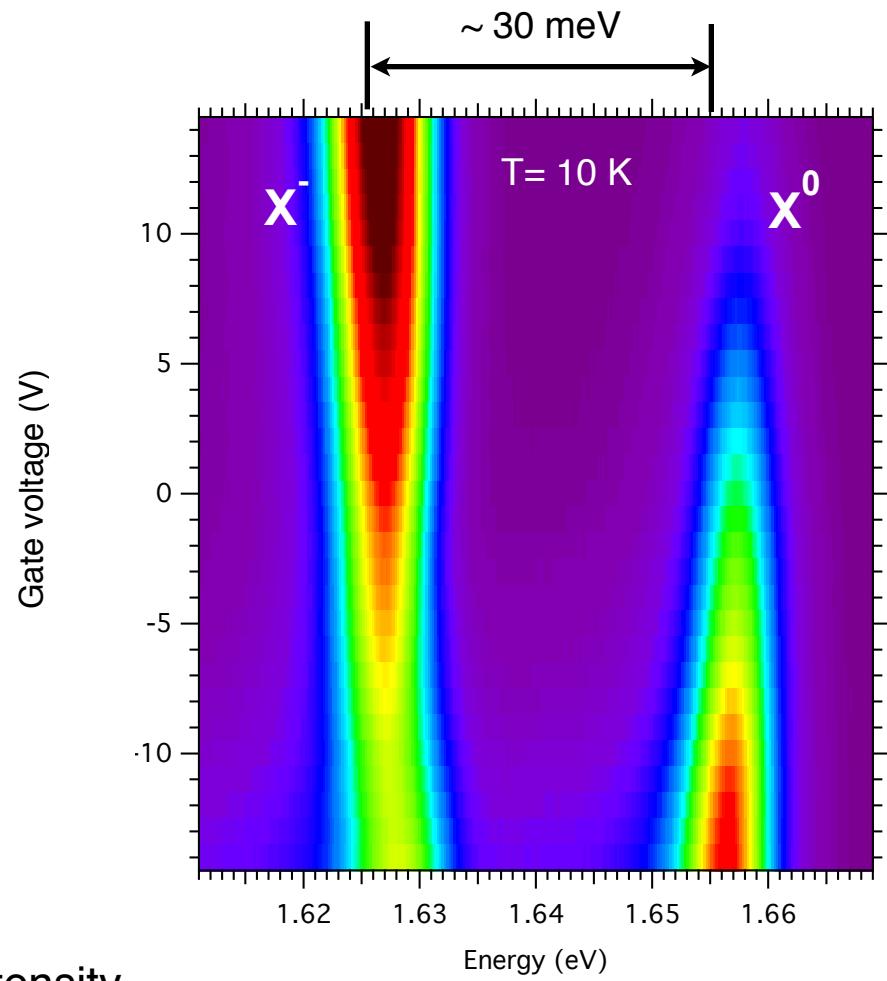
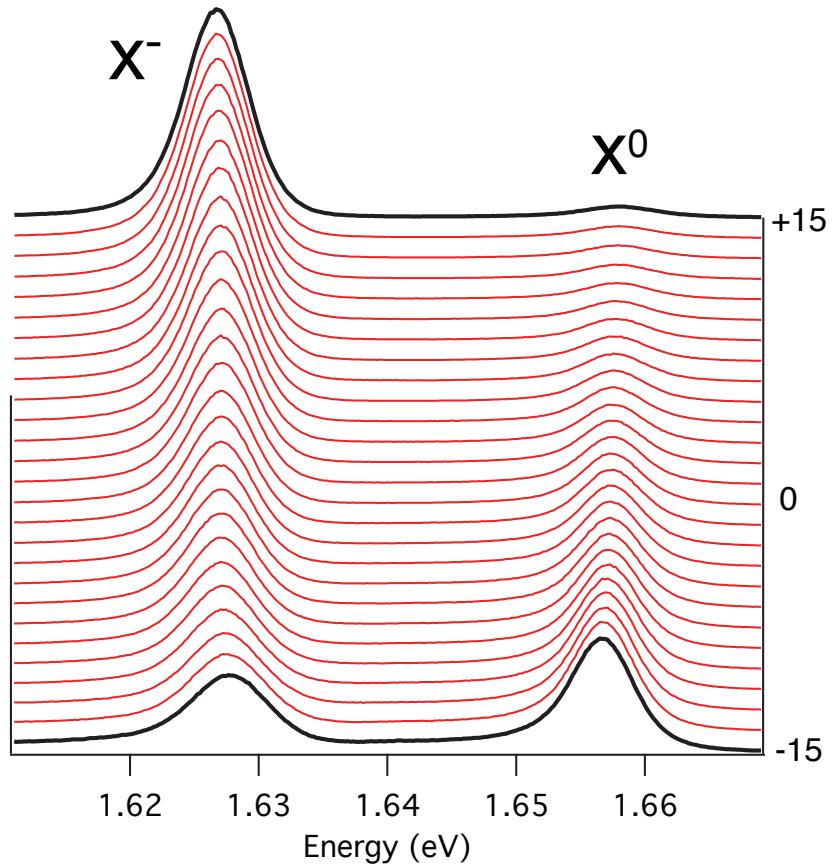
Gate voltage dependence



First shown by T.Heinz' (MoSe₂) and X.Xu's (MoSe₂) groups

Mak et al. Nature Mat., 12, 207 (2013)
Ross et al. Nature Comm., 4:1474 (2013)

Zero-field PL vs gate voltage



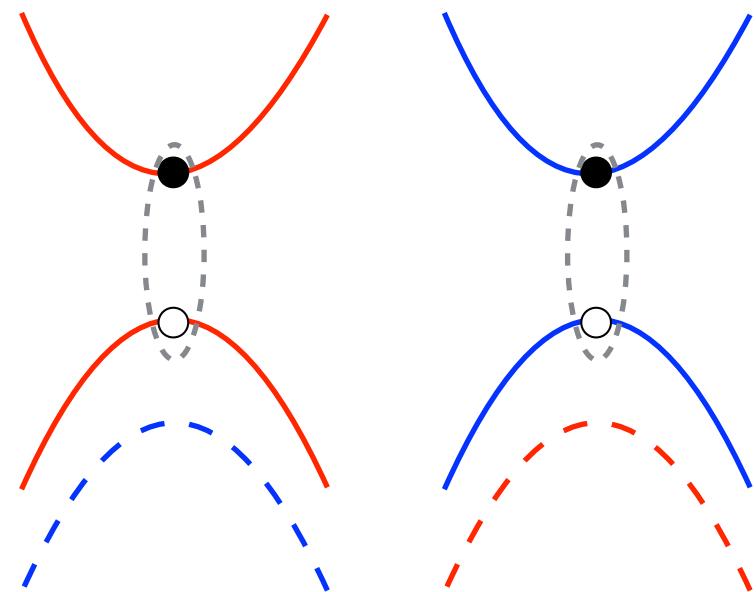
- ▶ Low-doping regime : X^- and X^0 have similar intensity
- ▶ High-doping regime : X^- dominates

Sample 415

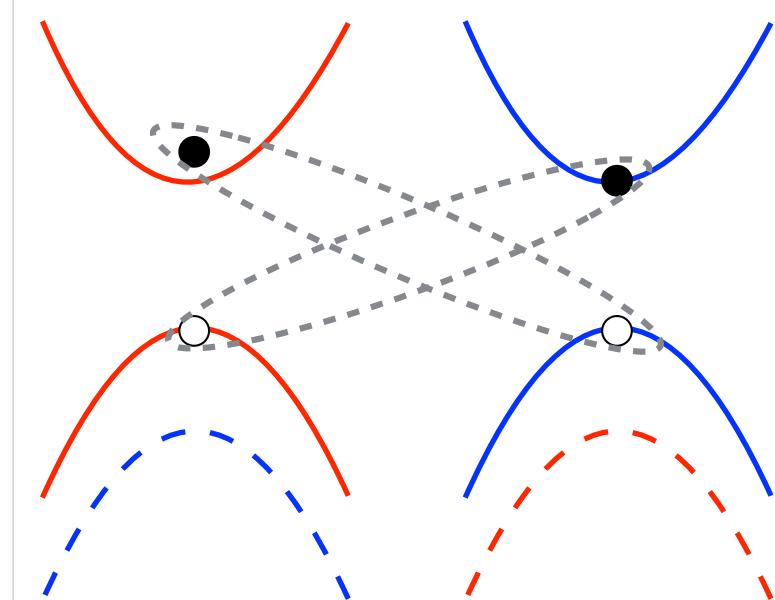
Excitons in a monolayer MoSe₂

X0 exciton : neutral exciton

“Bright”



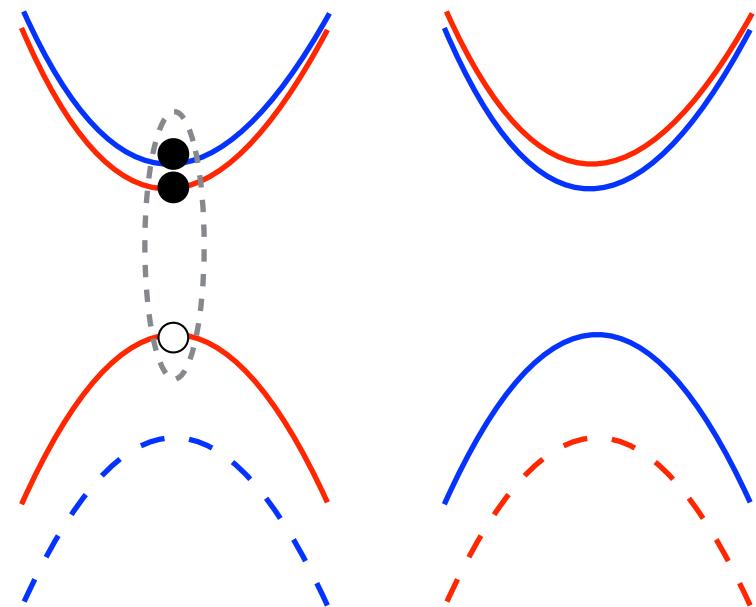
“Dark”



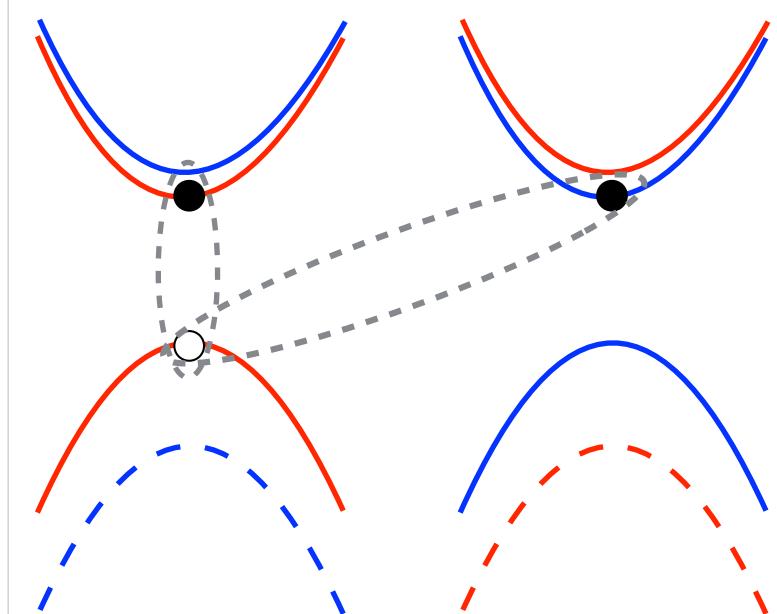
Excitons in monolayer MoSe₂

X-exciton : negatively charged trion

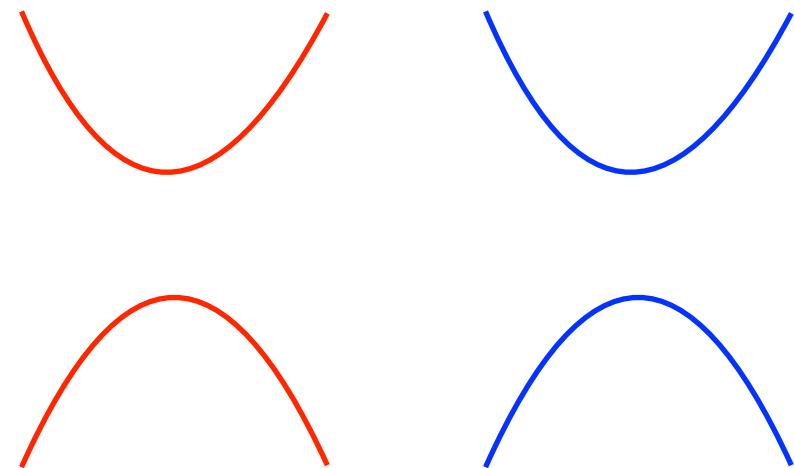
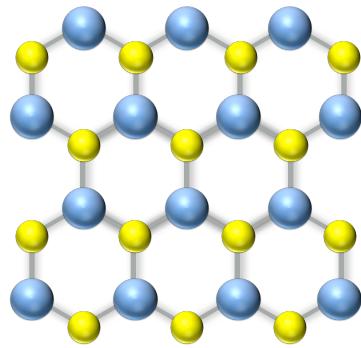
“Bright” intra-valley exciton



“Bright” inter-valley exciton



Valley Zeeman effect

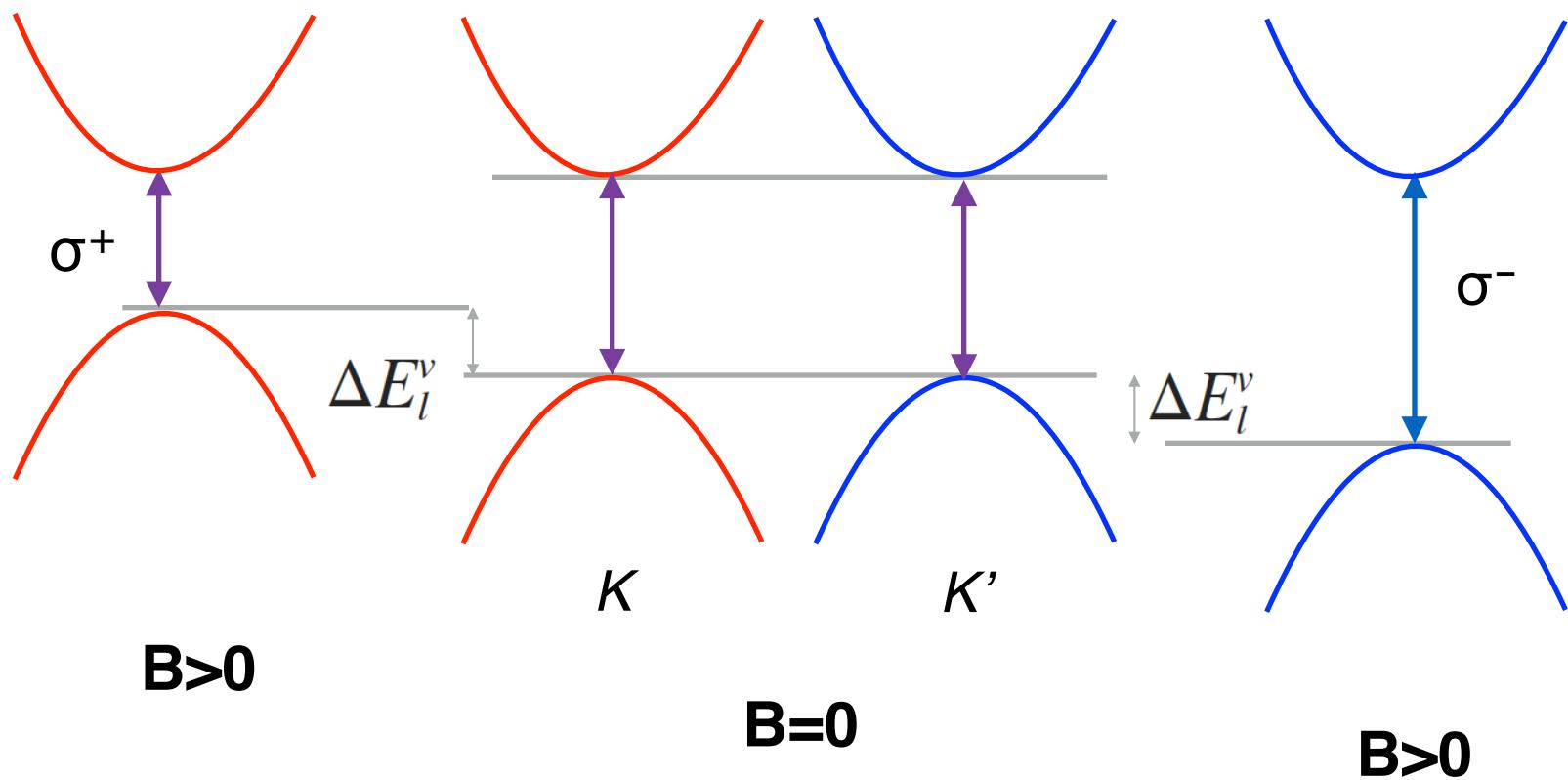


$$\Delta E_Z = E_s^{c/v} + \Delta E_l^{c/v} + \Delta E_k^{c/v}$$

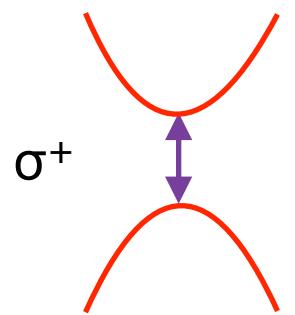
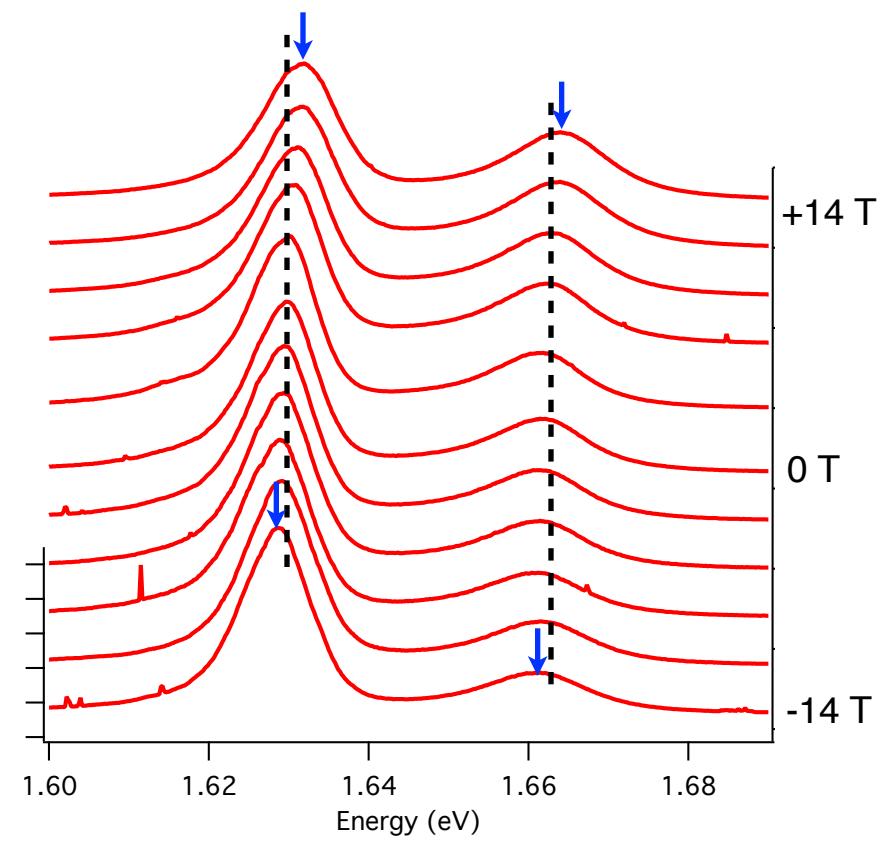
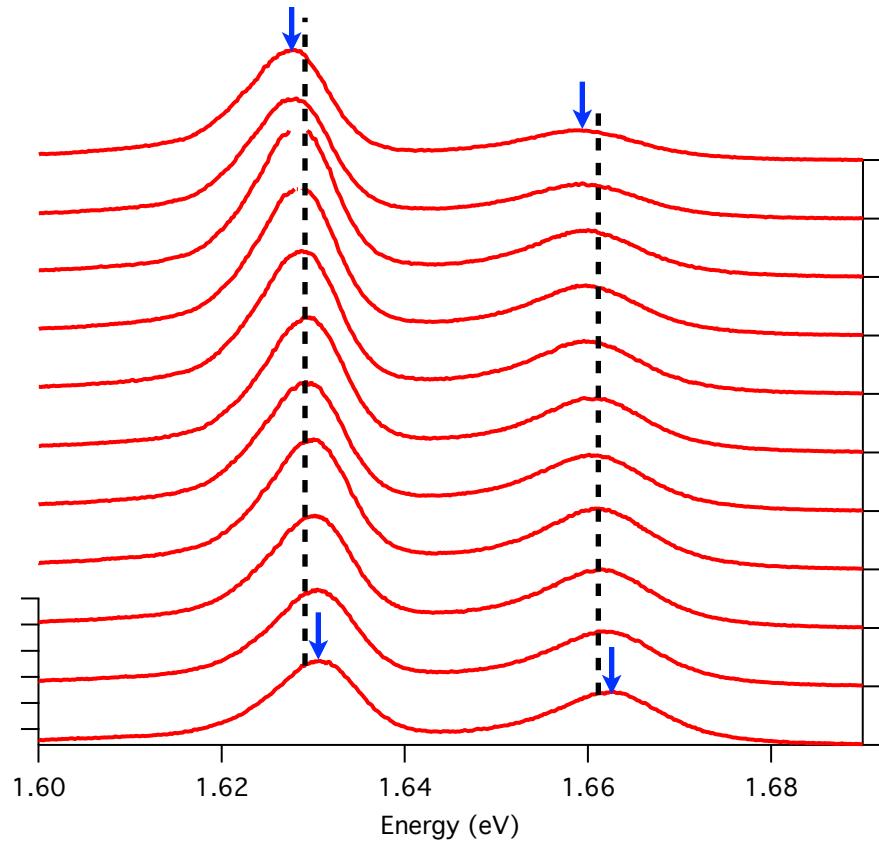
| | K valley | | K' valley | |
|---|----------------|----------------|----------------|----------------|
| | CB | VB | CB | VB |
| Spin | $-\mu_B$ | $-\mu_B$ | $+\mu_B$ | $+\mu_B$ |
| Atomic d-orbitals (intracellular) | 0 | $-2\mu_B$ | 0 | $+2\mu_B$ |
| Phase winding of Bloch function (intercellular) , $\alpha = m_0/m_{C,V}$ | $-\alpha\mu_B$ | $-\alpha\mu_B$ | $+\alpha\mu_B$ | $+\alpha\mu_B$ |

Valley Zeeman effect

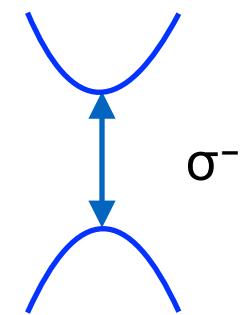
$$\Delta E_Z = \cancel{\Delta E_s^{c/v}} + \Delta E_l^{c/v} + \cancel{\Delta E_k^{c/v}} \approx 4\mu_B B$$



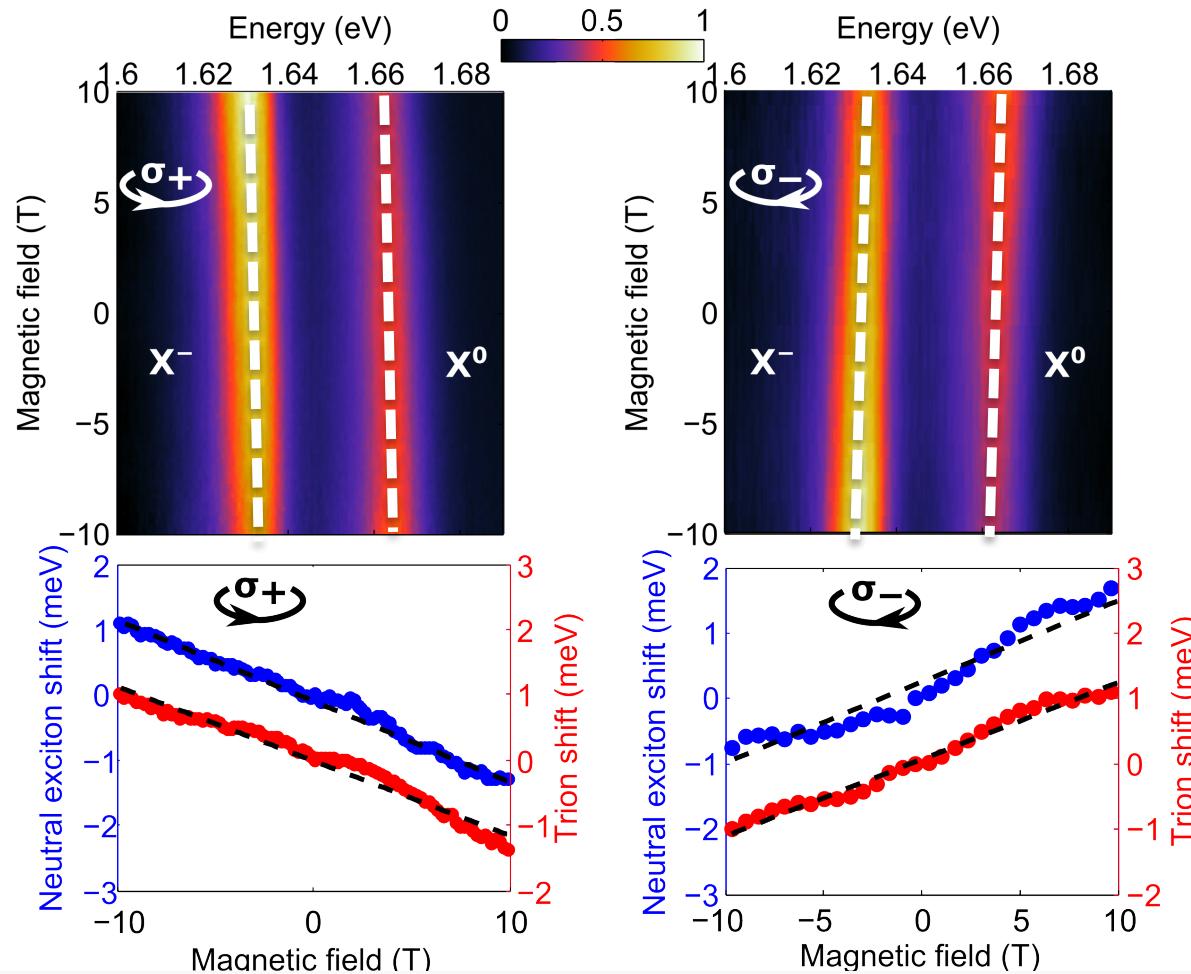
Valley Zeeman effect in a monolayer MoSe₂ : low carrier density



Valley degeneracy is lifted



Zeeman shift of exciton peaks



| | Experimental slope |
|-------|--------------------------|
| X^0 | $\pm 0.12 \text{ meV/T}$ |
| X^- | $\pm 0.12 \text{ meV/T}$ |

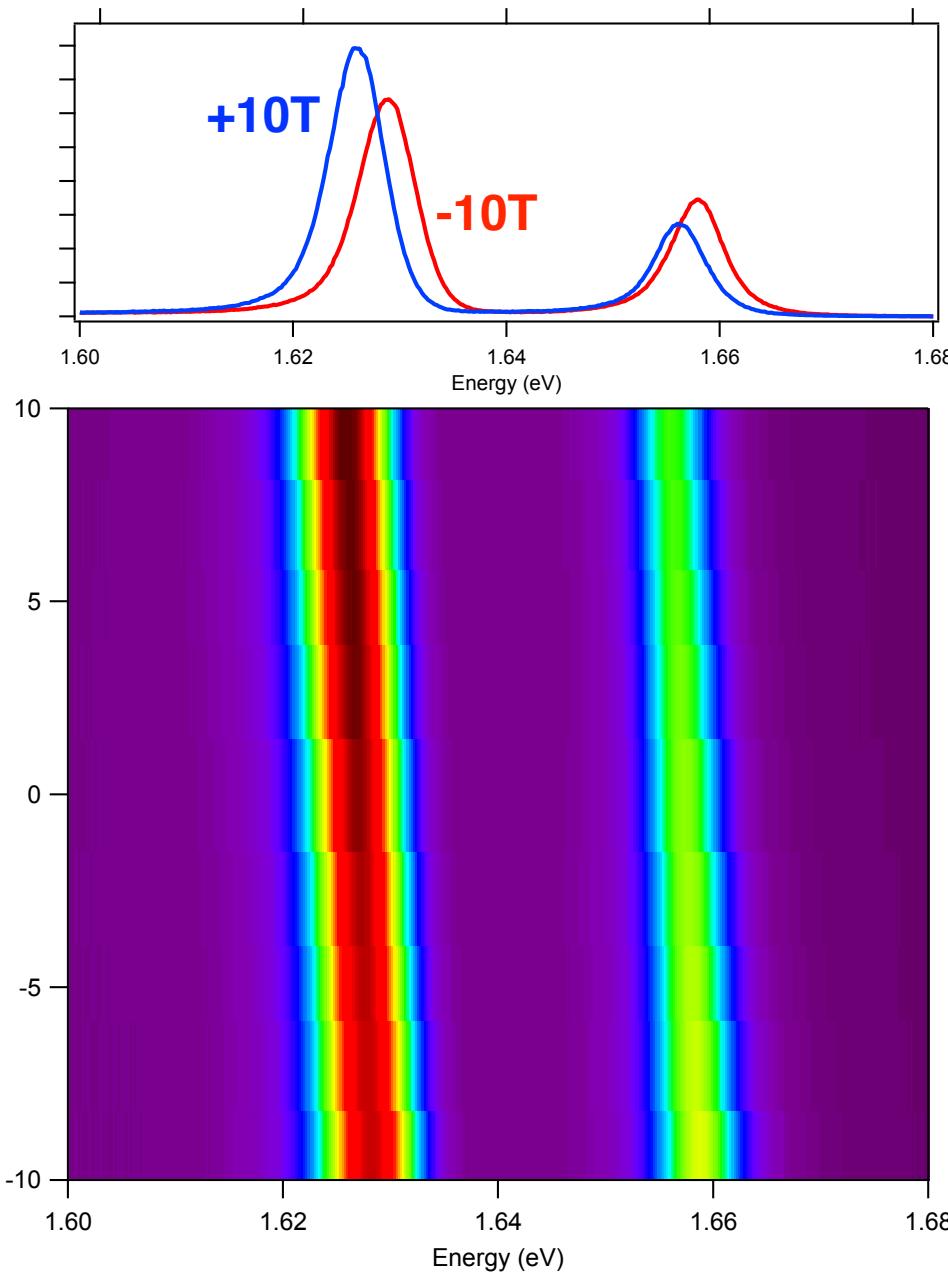
$$2\mu_B = 0.116 \text{ meV/T}$$

$$E_{X0} = E^c - E^v - E_{X0}^b$$

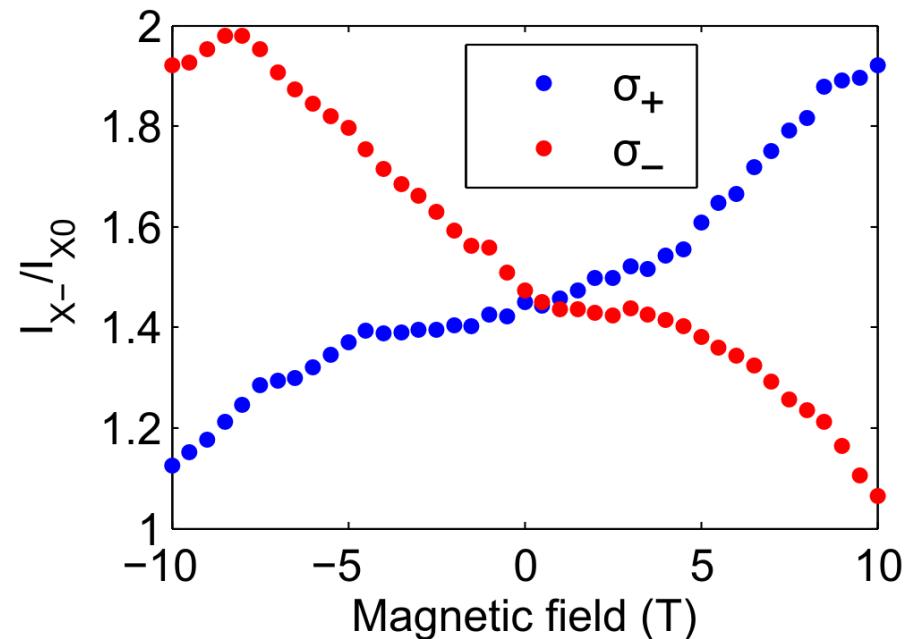
$$E_{X-} = E^c - E^v - E_{X0}^b - E_{X-}^b$$

- Valley degeneracy is lifted due to the contribution from the valence band atomic orbitals, resulting in total Landé factor of 4.1
- Binding energies are not influenced by the magnetic field at low densities

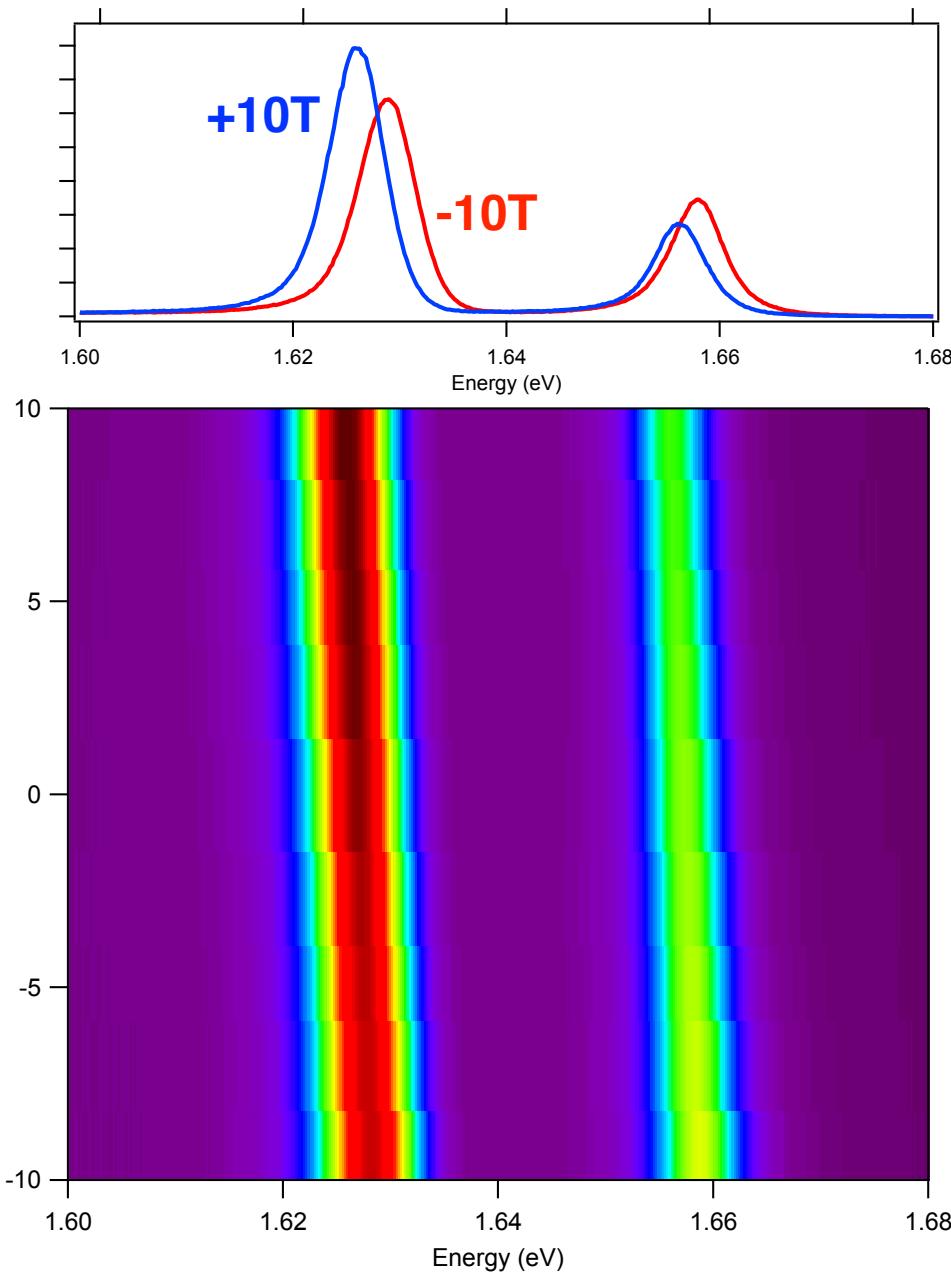
Variation of relative intensity



- The relative intensities of X– and X₀ varies monotonically with magnetic field
- The trend is reversed for the opposite valleys

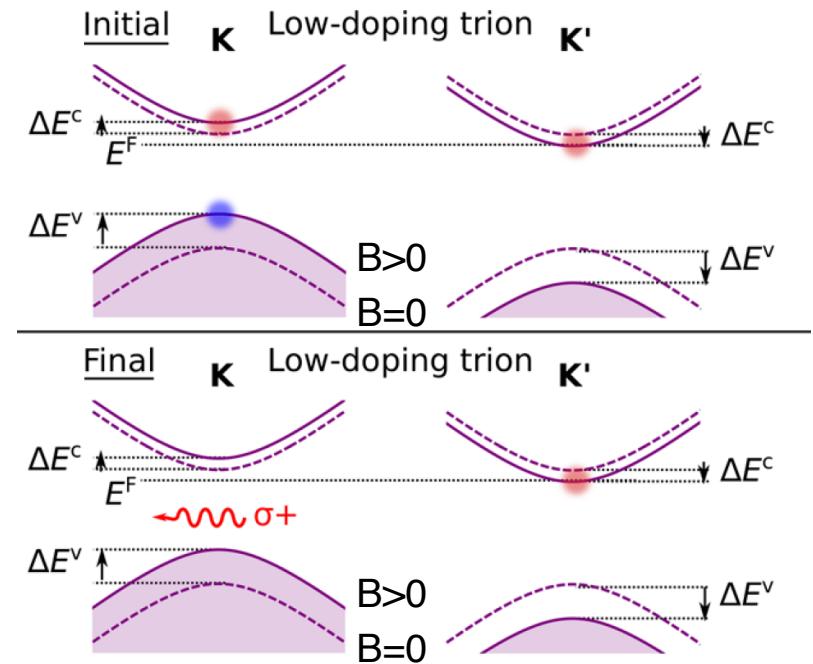


Trion configuration

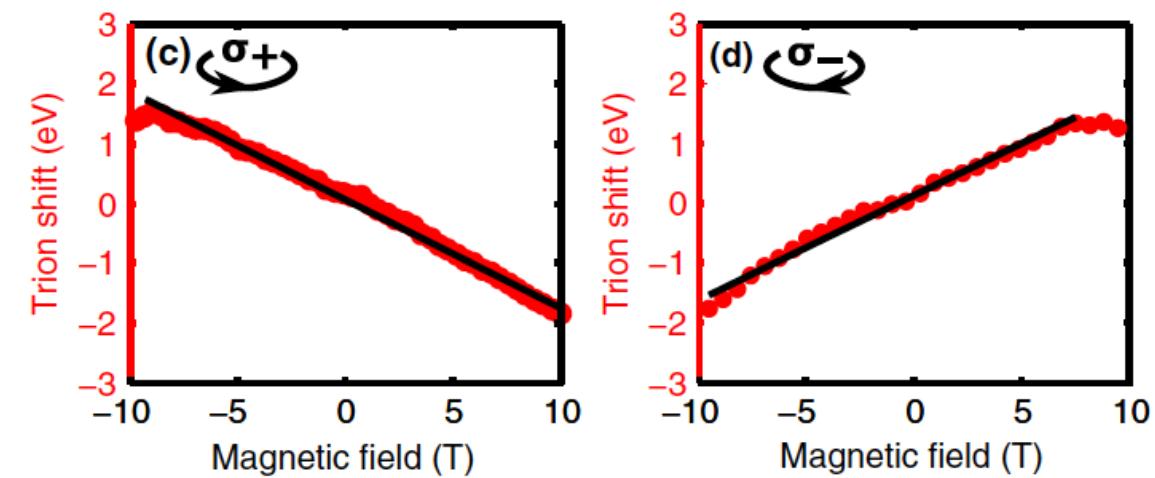
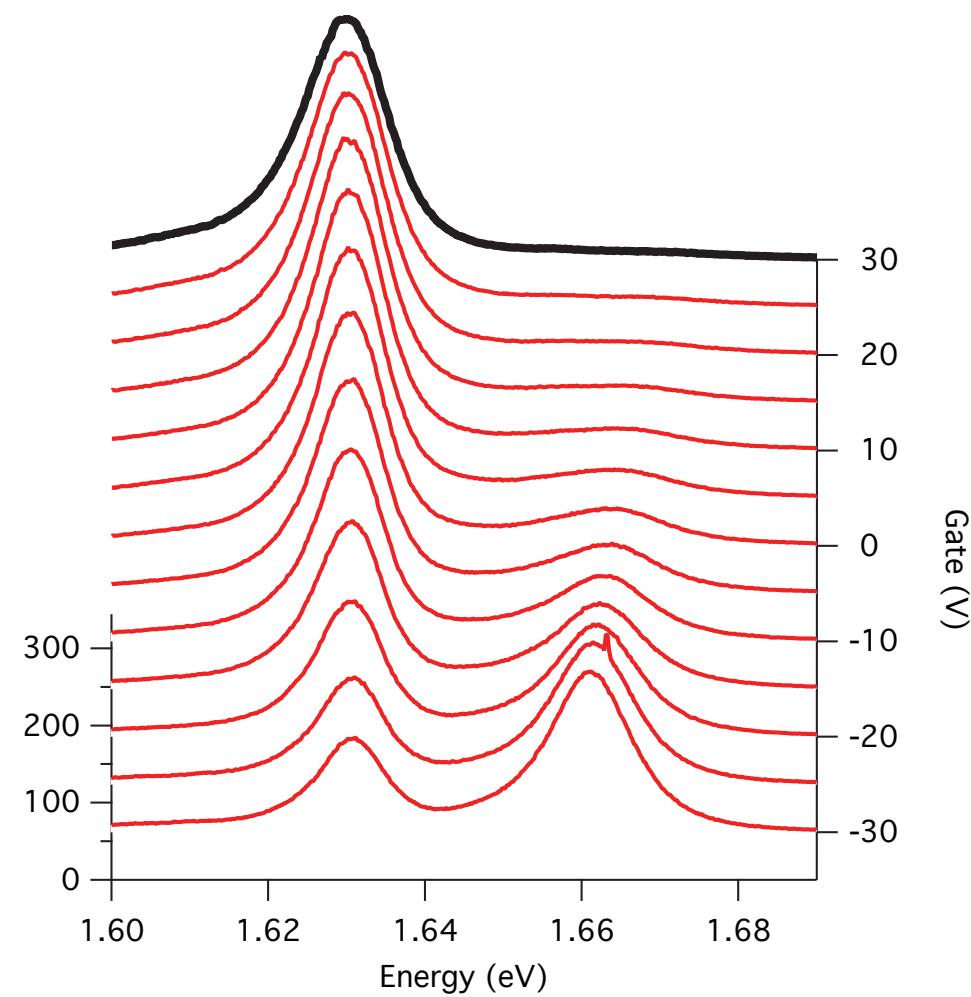


- The relative intensities of X– and X₀ varies monotonically with magnetic field
- The trend is reversed for the opposite valleys

Inter-valley trion

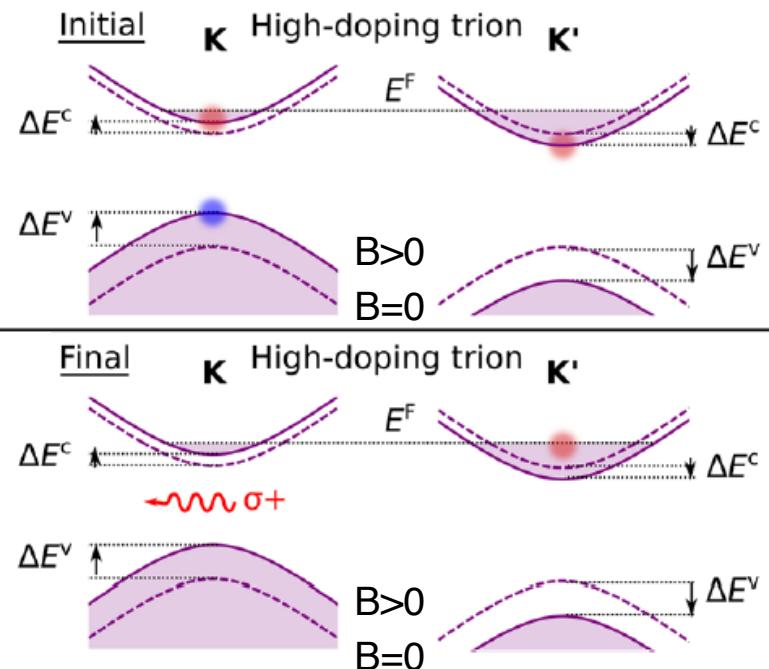


Trion emission at high carrier density



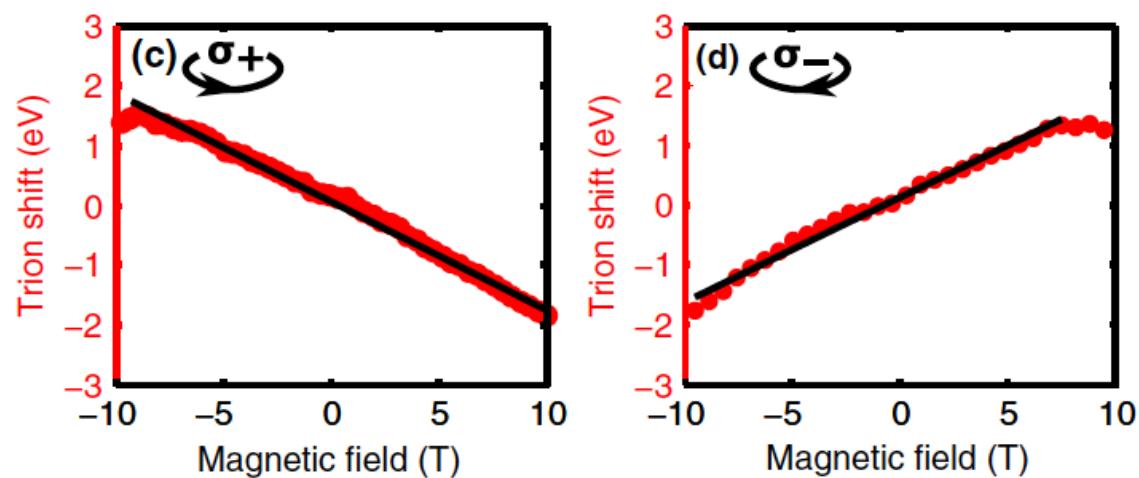
- The slope is **0.18 meV/T**, i.e. **50% increase** compared with **0.12 meV/T** in the regime of low carrier density
- Estimated carrier density of 3×10^{12} would cause the Fermi level to be ~ 10 meV above the CB edge

Trion emission at high carrier density



- At $E_F > E_C$, the trion Zeeman shift is expected to follow total VB contribution only ($5\mu_B$), which would result in **0.29 meV/T**.

???



- The slope is **0.18 meV/T**, i.e. **50% increase** compared with **0.12 meV/T** in the regime of low carrier density
- Estimated carrier density of 3×10^{12} would cause the Fermi level to be ~ 10 meV above the CB edge

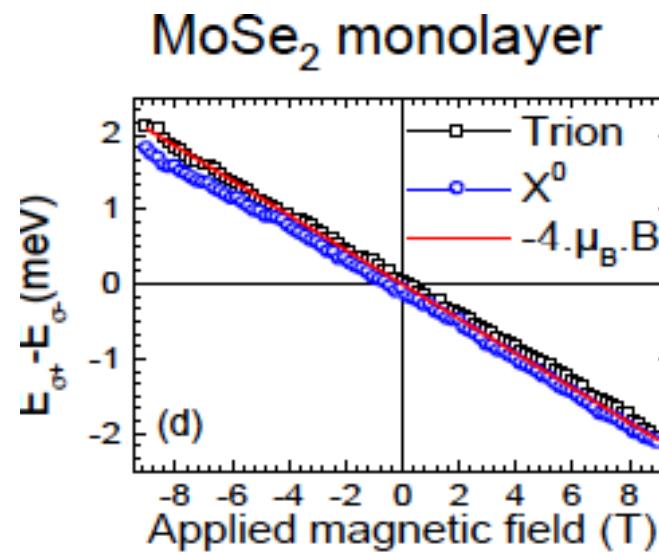
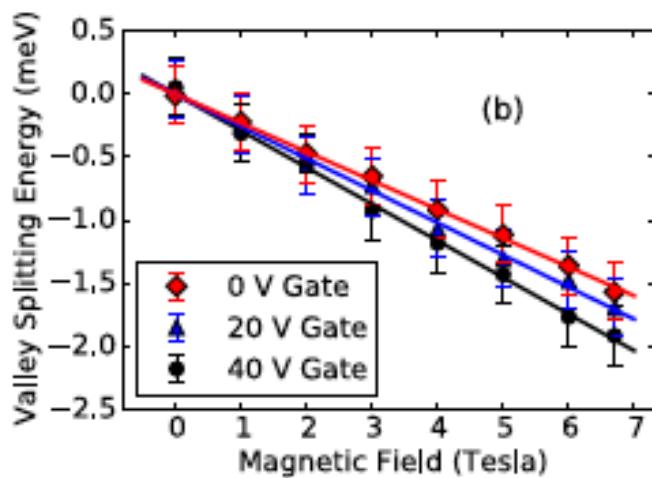
Related works on valley Zeeman effect in monolayer TMDs

Aivazian, G., et al. (Univ. of Wash.)
Magnetic control of valley pseudospin in monolayer WSe₂.
Nature Physics, **11**(2), 148 (2015)

Srivastava, A., et al. (ETH, EPFL)
Valley Zeeman effect in elementary optical excitations of monolayer WSe₂.
Nature Physics, **11**(2), 141 (2015)

MacNeill, D., et al. (Cornell)
Breaking of Valley Degeneracy by Magnetic Field in
Monolayer MoSe₂.
Physical Review Letters, **114**, 037401 (2015)

Wang, G., et al. (Toulouse, Ioffe)
Magneto-optics in transition metal diselenide monolayers.
arXiv:1503.04105v1 (2015)



Valley splitting and polarization in monolayer MoSe₂

- Splitting of K/K' valleys by application of perpendicular magnetic field (tuning valley DoF)
- Charge imbalance in different valleys for doped samples – creation of steady-state valley polarization
- Intervalley configuration is the lower energy state for the trion
- Variation in the trion emission energy X-(B) with at high doping (call for more experimental and theoretical studies)